

In the Claims

Claims 1-107 (cancelled).

Claim 108 (original): A capacitor construction, comprising:

- an electrically insulative material;
- a region extending into the material, the material comprising a periphery around the region;
- agglomerates along the periphery; the agglomerates comprising one or more noble metals;
- a first conductive layer within the region and extending over agglomerates;
- a dielectric layer over the first conductive layer; and
- a second conductive layer over the dielectric layer; the second conductive layer being capacitively coupled with the first conductive layer.

Claim 109 (original): The capacitor construction of claim 108 wherein the insulative material comprises borophosphosilicate glass.

Claim 110 (original): The capacitor construction of claim 108 wherein the insulative material comprises phosphosilicate glass.

Claim 111 (original): The capacitor construction of claim 108 wherein the insulative material comprises borophosphosilicate glass having one or both of silicon dioxide and aluminum oxide thereover.

Claim 112 (original): The capacitor construction of claim 108 further comprising cavities extending into the periphery between the agglomerates, and wherein the first conductive layer extends into the cavities.

Claim 113 (original): The capacitor construction of claim 108 wherein the one or more noble metals are selected from the group consisting of Pt, Rh, Ru, Pd and Ir.

Claim 114 (original): The capacitor construction of claim 108 wherein the agglomerates consist essentially of the one or more noble metals.

Claim 115 (original): The capacitor construction of claim 108 wherein the agglomerates consist essentially of Pt.

Claim 116 (original): The capacitor construction of claim 108 incorporated into a DRAM array.